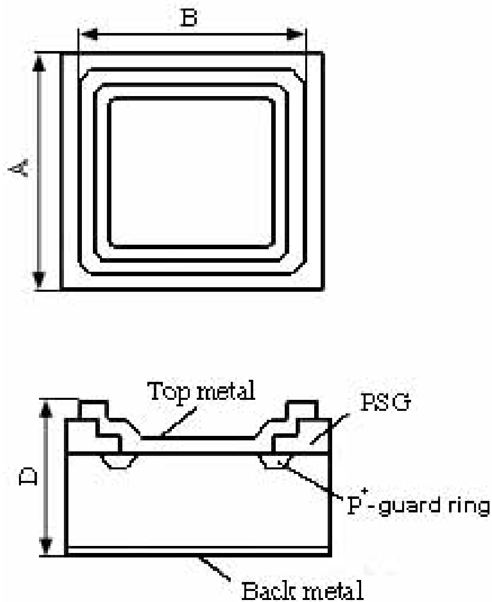
SCHOTTKY DIODES KDN-10060A.
PRELIMINARY

Rev.1. Feb. 2010

VSP-MIKRON

10A/60V. Die Size-98mil.

Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ I_R=10mA	V_{BR}	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25˚C, I_F=10,0A	V_F	V	0,65	0,62
Maximum Reverse Current @ 25˚C, V_R=65V 25˚C, V_R=60V 125˚C, V_R=60V	I_R	mA	- 0,250 140,0	0,250 0,180 130,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	160	-
Peak Repetitive Reverse Surge Current @2,0μs, f=1kHz., T_J<150˚C.	I_{RRM}	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/μS	10.000	
Operating Junction Temperature	T_J	˚C	150	



DIM	ITEM	μm
A_X A_y	Wafer Form Die Size	2500 2500
B_X B_y	Top Metal Size	2360 2360
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) ***Al-Ni-Ag*** – for Soldering.
*Backside metal: **Ti-Ni-Ag**.*